

TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT MULTI CHIP

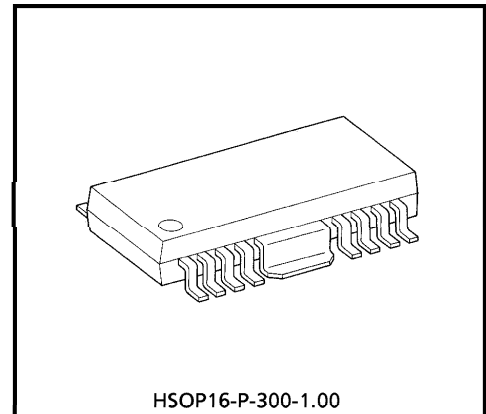
TD62M8603F

8CH LOW SATURATION VOLTAGE SOURCE DRIVER

TD62M8603F is Multi Chip IC incorporates 8 low saturation discrete (2SA1203) transistors.
 This IC is suitable for a battery use motor drive and LED display module applications.

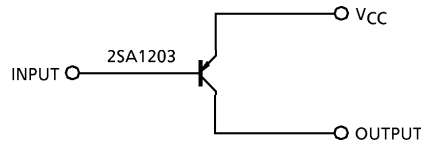
FEATURES

- Suitable for Motor drive circuit and LED display module
- External Bias Resistor
- Low Saturation Voltage
 - $V_{CE(sat)} = 0.10V$ (Typ.) at $I_C = 0.5A$
 - $V_{CE(sat)} = 0.20V$ (Max.) at $I_C = 1.5A$
- HSOP16 power small package sealed

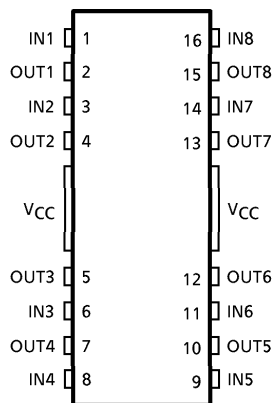


Weight : 0.50g (Typ.)

BLOCK DIAGRAM



PIN CONNECTION (TOP VIEW)



961001EBA2

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	- 30	V
Breakdown Voltage	V _{CBO}	- 30	V
	V _{CEO}	- 30	
	V _{EBO}	- 5	
Output Current	I _O	- 1.5	A / ch
	I _O (PEAK)	(Note) - 3.0	
Base Current	I _B	- 0.3	A
Power Dissipation	P _D	900	mW
Junction Temperature	T _j	150	°C
Operating Temperature	T _{opr}	- 40~85	°C
Storage Temperature	T _{stg}	- 55~150	°C

(Note) T = 10ms single pulse

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

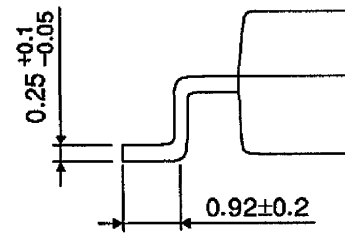
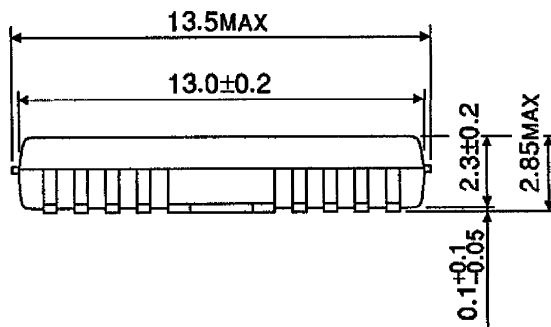
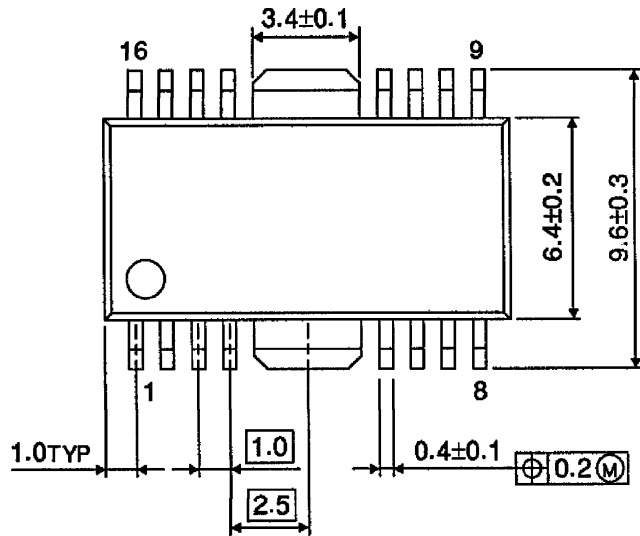
CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Gain	h _{FE} (1)	—	V _{CE} = - 2V, I _C = - 0.5A	160	—	320	—
	h _{FE} (2)	—	V _{CE} = - 2V, I _C = - 1.5A	50	100	—	
Saturation Voltage	V _{CE} (sat)	—	I _C = - 0.5A, I _B = - 10mA	—	- 0.1	- 0.50	V
			I _C = - 1.5A, I _B = - 30mA	—	—	- 2.0	
Transition Frequency	f _T	—	V _{CE} = - 2V, I _C = - 0.5A	—	120	—	MHz
Leakage Current	I _{OL}	—	V _{CC} = - 30V	—	0	- 5	μA
Base-Emitter Forward Voltage	V _{BE}	—	V _{CE} = - 2V, I _C = - 0.5A	—	—	- 1.0	V

PRECAUTIONS for USING

Utmost care is necessary in the design of the output line, V_{CC} and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

OUTLINE DRAWING
HSOP16-P-300-1.00

Unit : mm



Weight : 0.50g (Typ.)